

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method of manufacturing a semiconductor device, the method comprising steps of:

forming a first metal film having a reducing property on a semiconductor substrate;

thermal treating the resulting semiconductor substrate and the first metal film supported thereon for reducing a native oxide film naturally formed on the semiconductor substrate and for forming a first silicide film on the semiconductor substrate in at least a source/drain region;

after forming the first silicide film via the first metal film in the source/drain region, removing an unreacted portion of the first metal film selectively;

forming a second metal film on the semiconductor substrate over and contacting at least the first silicide film; and

thermal treating the resulting semiconductor substrate and the second metal film supported thereon for forming a second silicide film on a surface of the semiconductor substrate in at least said source/drain region which includes a region where the first silicide film is formed.

2. (*Previously presented*) A method of manufacturing a semiconductor device according to claim 1, wherein the first metal film comprises titanium.
3. (*Previously presented*) A method of manufacturing a semiconductor device according to claim 1, wherein the second metal film comprises cobalt.
4. (*Previously presented*) A method of manufacturing a semiconductor device according to claim 1, wherein said thermal treating for reducing the native oxide film and forming the first silicide film is carried out at a temperature of 500°C or less.
5. (*Original*) A method of manufacturing a semiconductor device according to claim 4, wherein the first silicide film is formed to have a thickness of 1 to 10 nm.
6. (*Original*) A method of manufacturing a semiconductor device according to claim 1, wherein the second metal film is formed to have a thickness of 1 to 10 nm.
7. (*Original*) A method of manufacturing a semiconductor device according to claim 1, further comprising a step of forming a protection film after the step of forming the second metal film and before the step of heat-treating for forming a second silicide film.

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8. (*Original*) A method of manufacturing a semiconductor device according to claim 7, wherein the protection film is a titanium nitride film.

9. (*Original*) A method of manufacturing a semiconductor device according to claim 1, further comprising a step of oxidizing the semiconductor substrate in a mixed solution of hydrochloric acid, hydrogen peroxide solution and water before the step of forming the first metal film.

10. (*Previously presented*) A method of manufacturing a semiconductor device according to claim 1, further comprising heating the substrate when the first metal film is formed and this heating of the substrate also serves as the thermal treating for reducing the native oxide film and forming the first silicide film.

11. (*Original*) A method of manufacturing a semiconductor device according to claim 1, wherein a MOSFET is formed.

12. (*Currently amended*) A semiconductor device manufactured by a method comprising steps of:

forming a first metal film having a reducing property on a semiconductor substrate;

thermal treating the resulting semiconductor substrate for reducing a native oxide film naturally formed on the semiconductor substrate and for forming a first silicide film on the semiconductor substrate;

removing an unreacted first metal film selectively;

forming a second metal film on the semiconductor substrate; and

thermal treating the resulting semiconductor substrate for forming a second silicide film on a surface of the semiconductor substrate in at least a source/drain region of the semiconductor device which includes a region where the first silicide film is formed.

13. (*Currently amended*) A method of making a semiconductor device, the method comprising:

forming a first metal inclusive film having a reducing property over at least a semiconductor substrate;

after forming the first metal inclusive film, thermal treating at least the semiconductor substrate to reduce a native oxide film formed over at least the semiconductor substrate and to form a first silicide film over at least the semiconductor substrate;

forming a second metal inclusive film over at least semiconductor substrate and contacting the first silicide film; and

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after forming the second metal inclusive film, thermal treating at least the semiconductor substrate to form a second silicide film on at least a source/drain region of the semiconductor device which includes a region where the first silicide film was formed.

14-15. (*Canceled*)

16. (*Previously presented*) The method of claim 13, further comprising removing at least part of an unreacted portion of the first metal film after forming the first silicide film but before forming the second silicide film.